60V PNP SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT89

Features

- BV_{CEO} > -60V
- High current capability Max Continuous Current I_C = -4.3A
- Low saturation voltage $V_{CE(sat)}$ < -65mV @ I_C = -1A
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Application

- **Emergency lighting circuits**
- Motor driving (including DC fans)
- Backlight inverters
- Power switches
- MOSFET gate drivers

Mechanical Data

- Case: SOT89
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Rating 94V-0
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (Approximate)

SOT89

Top View

Device symbol

Pin-out Top

Ordering Information (Note 3 & 4)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2012ZTA	Commercial	951	7	12	1,000
ZXTP2012Z-13R	Commercial	951	7	12	4,000
ZXTP2012ZQTA	Automotive	951	7	12	1,000

Notes:

- 1. No purposefully added lead.
- 2. Halogen and Antimony Free. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com 3. For packaging details, go to our website at http://www.diodes.com
- 4. Products with Q-suffix are automotive grade

Marking Information

951 = Product Type Marking Code

Maximum Ratings @T_A = 25℃ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	Ic	-4.3	Α
Peak Pulse Current	I _{CM}	-15	Α

Thermal Characteristics @T_A = 25℃ unless otherwise specified

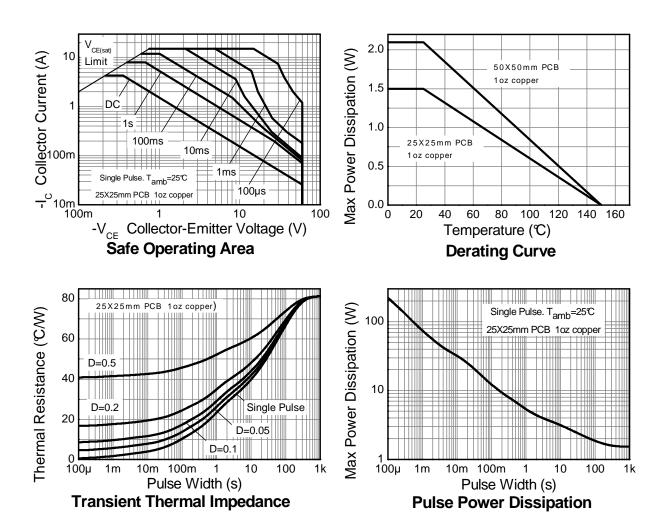
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear derating factor	P _D	1.5 12	wW/℃
Power Dissipation (Note 6) Linear derating factor	P _D	2.1 16.8	W W W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	60	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	3.23	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

Notes:

- 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions. 7. Thermal resistance from junction to solder-point (on the exposed collector pad).



Thermal Characteristics



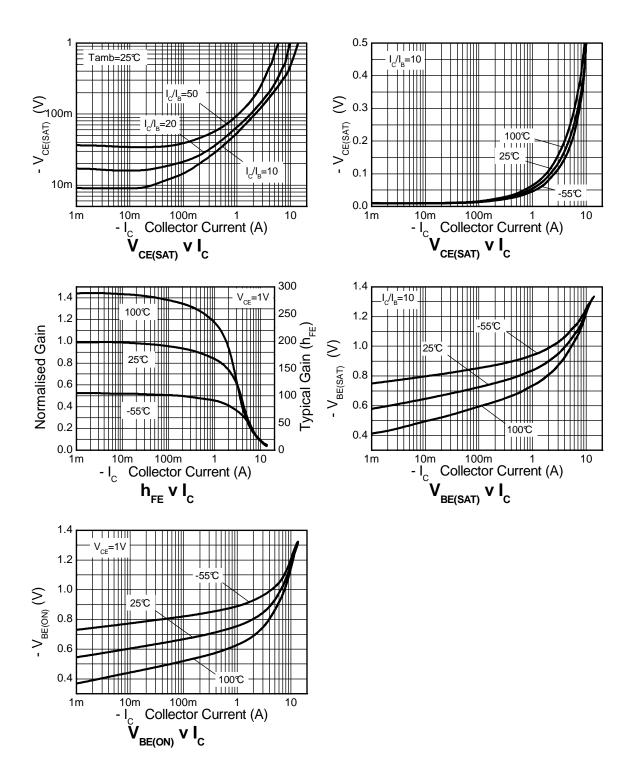
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CER}	-100	-120	-	V	I _C = -1μA, R _B ≤1kΩ
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CEO}	-60	-80	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100℃
Collector Cutoff Current	I _{CER} R≤1kΩ	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100℃
Emitter Cutoff Current	I _{EBO}	-	< -1	-10	nA	V _{EB} = -6V
DC current transfer Static ratio (Notes 8)	h _{FE}	100 100 45 10	250 200 90 25	300		I _C = -10mA, V _{CE} = -1V I _C = -2A, V _{CE} = -1V I _C = -5A, V _{CE} = -1V I _C = -10A, V _{CE} = -1V
Collector-Emitter Saturation Voltage (Notes 8)	V _{CE(sat)}	-	-14 -50 -75 -160	-20 -65 -110 -215	mV	$I_C = -100$ mA, $I_B = -10$ mA $I_C = -1$ A, $I_B = -100$ mA $I_C = -2$ A, $I_B = -200$ mA $I_C = -5$ A, $I_B = -500$ mA
Base-Emitter Saturation Voltage (Notes 8)	V _{BE(sat)}	-	-950	-1050	mV	I _C = -5A, V _{CE} = -1V
Base-Emitter Turn-on Voltage (Notes 8)	$V_{BE(on)}$	-	-840	-950	mV	$I_C = -5A$, $V_{CE} = -1V$
Transitional Frequency (Notes 8)	f _T	-	120	-	MHz	$I_C = -100 \text{mA}, V_{CE} = -10 \text{V},$ f = 50MHz
Output capacitance	C_{obo}	-	48	-	pF	$V_{CB} = -10V, f = 1MHz,$
Switching Time	t _{ON}	-	39 370	-	ns	$V_{CC} = -10V, I_{C} = -1A,$ $I_{B1} = I_{B2} = -100mA$

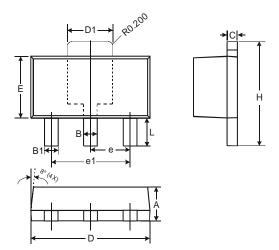
Notes: 8. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics

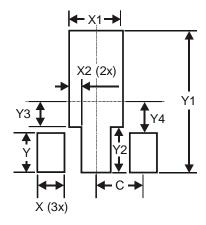


Package Outline Dimensions



SOT89				
Dim	Min Max			
Α	1.40 1.60			
В	0.44	0.62		
B1	0.35	0.54		
С	0.35	0.43		
D	4.40	4.60		
D1	1.52	1.83		
Е	2.29	2.60		
е	1.50 Typ			
e1	3.00 Typ			
Н	3.94	4.25		
L	0.89	1.20		
All Dimensions in mm				

Suggested Pad Layout



Dimensions	Value (in mm)
Х	0.900
X1	1.733
X2	0.416
Υ	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
С	1.500

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